PECVD-SIO2 standard recipe-1000A		
1. Chamber Clean (wet clean)	**2. Chamber clean+coat**	**3.SIO2 Deposition**
WET CLEAN	**30CLN_SO**	**SiO_10**
Wipe clean upper chamber walls with DI	step1: Initial t=10", p=2x10-2 T=250C	step1: Initial t=10"
Wipe off upper chamber walls with IPA	step2: N2 purge t=30" p=300mT	step2: N2 purge t=30"
	step3: evacuate, base pressure=2x10-2, t=10"	step3: evacuate, t=10"
	step4:loop	step4:loop
	step5:gass stabilization, t=30"	step5: SiO2 gass stabilization, t=30"
	step6:etch chamber, t=30'	step6:SiN deposition
	step7:evacuate, t=10"	step7:evacuate, t=10"
	step8:N2 purge	step8:N2 purge t=30"
	step9:evacuate	step9:evacuate t=10"
	step10:loop	step10:loop
	step11:SiO2 gass stabilization	
	step12:SiO2 deposition(200A coat)	
	step13:evacuate	
	step14:N2purge, t=30"	
	step15:end	